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United States Patent [19]

Nakayama et al.

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[54] SEMICONDUCTOR DEVICE

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[73] Assignee: Matsushita Electronics Corporation, Osaka, Japan

[**] Term: 14 Years

[21] Appl. No.: 69,590

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[30] Foreign Application Priority Data

Oct. 17, 1996 [JP] Japan 8-31320

[51] LOC (6) Cl. 13-03

[52] U.S. Cl. D13/182

[58] Field of Search D13/182; 174/52.4, 174/52.5; 257/690; 361/752, 798, 820

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[57] CLAIM

The ornamental design for a semiconductor device, as shown.

DESCRIPTION

FIG. 1 is a perspective view of the top, front and left side of a semiconductor device showing our new design;
 FIG. 2 is a perspective view of the bottom, rear and right side thereof;
 FIG. 3 is a front elevational view thereof;
 FIG. 4 is a top plan view thereof;
 FIG. 5 is a left side elevational view thereof;
 FIG. 6 is a right side elevational view thereof;
 FIG. 7 is a rear elevational view thereof; and
 FIG. 8 is a bottom plan view thereof.

1 Claim, 3 Drawing Sheets

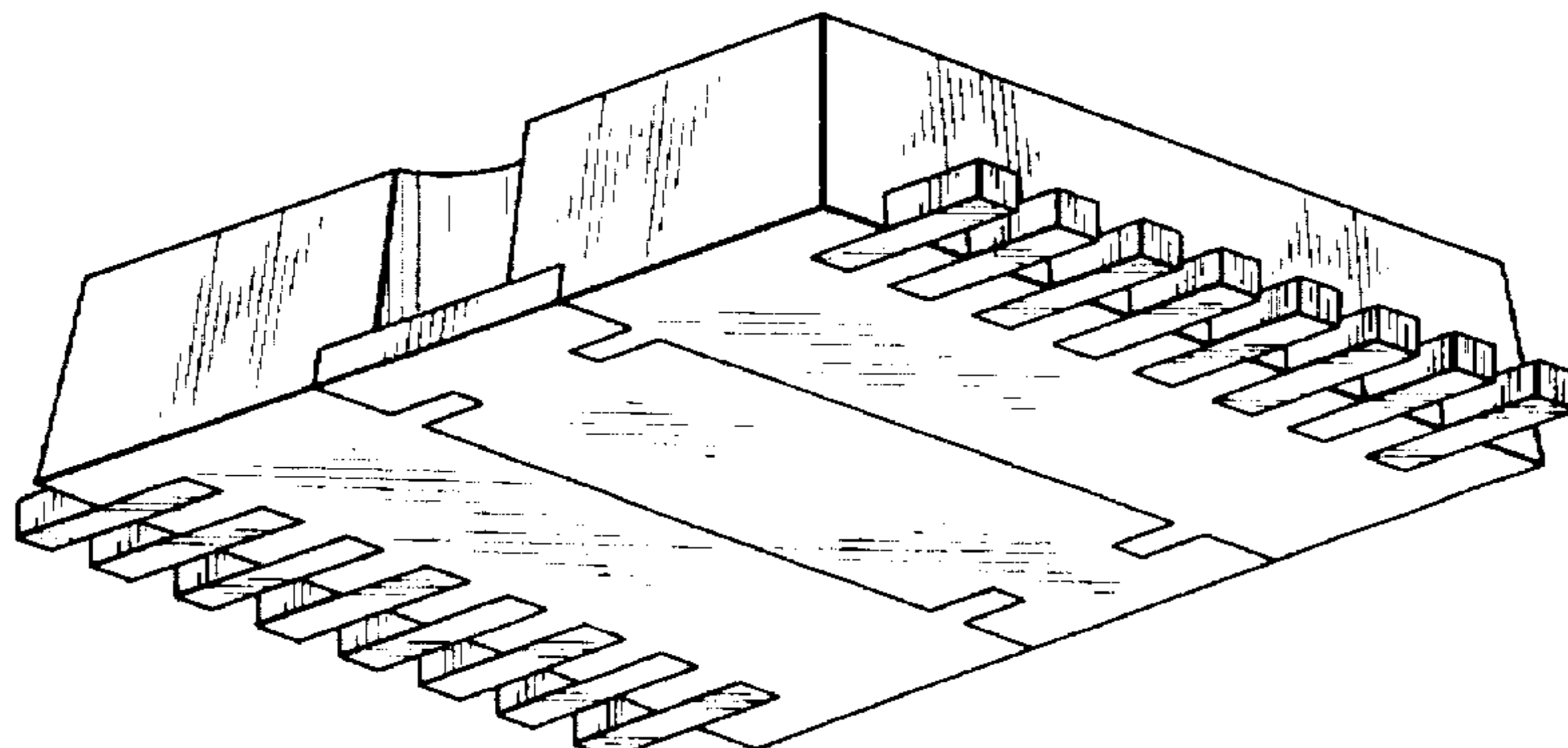
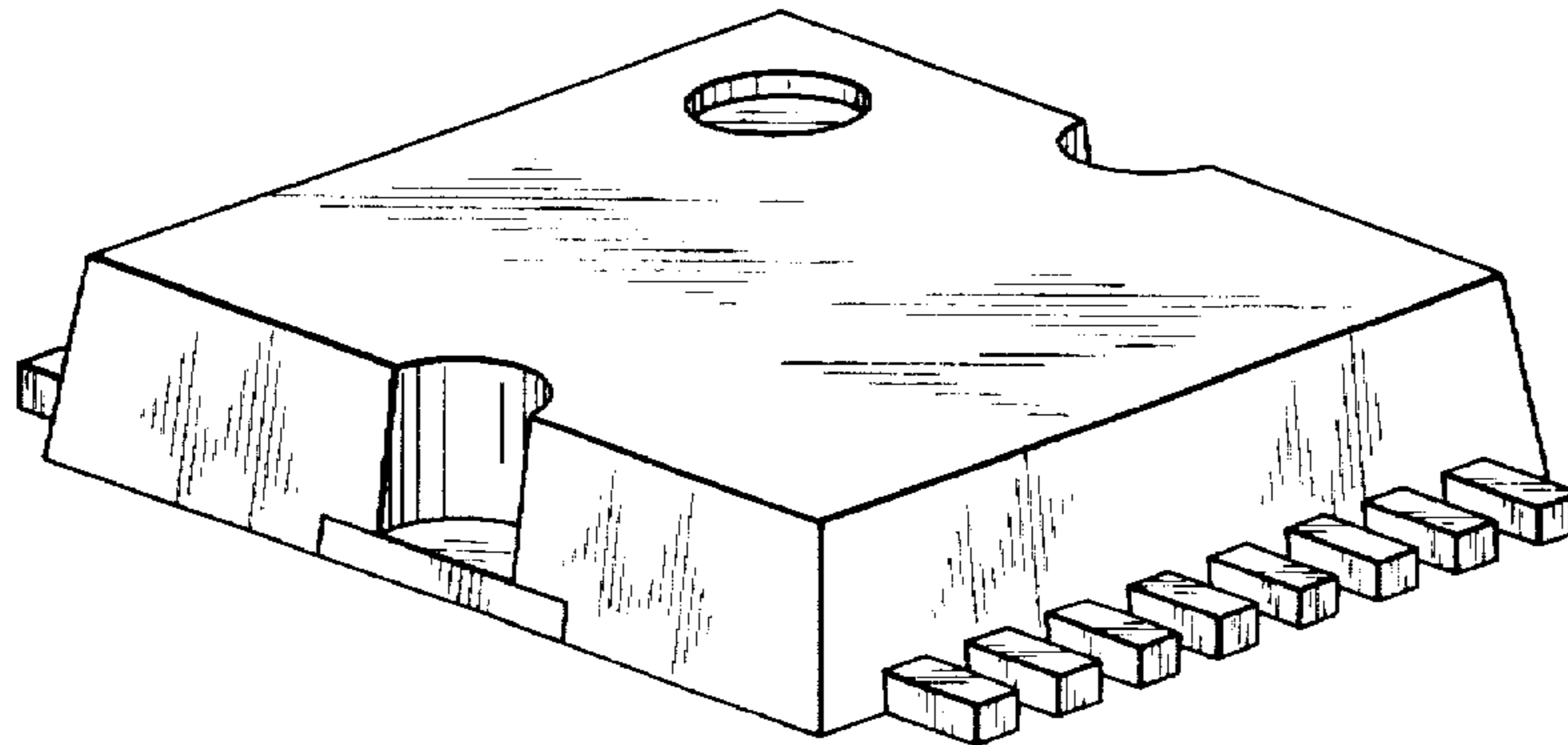


FIG. 1

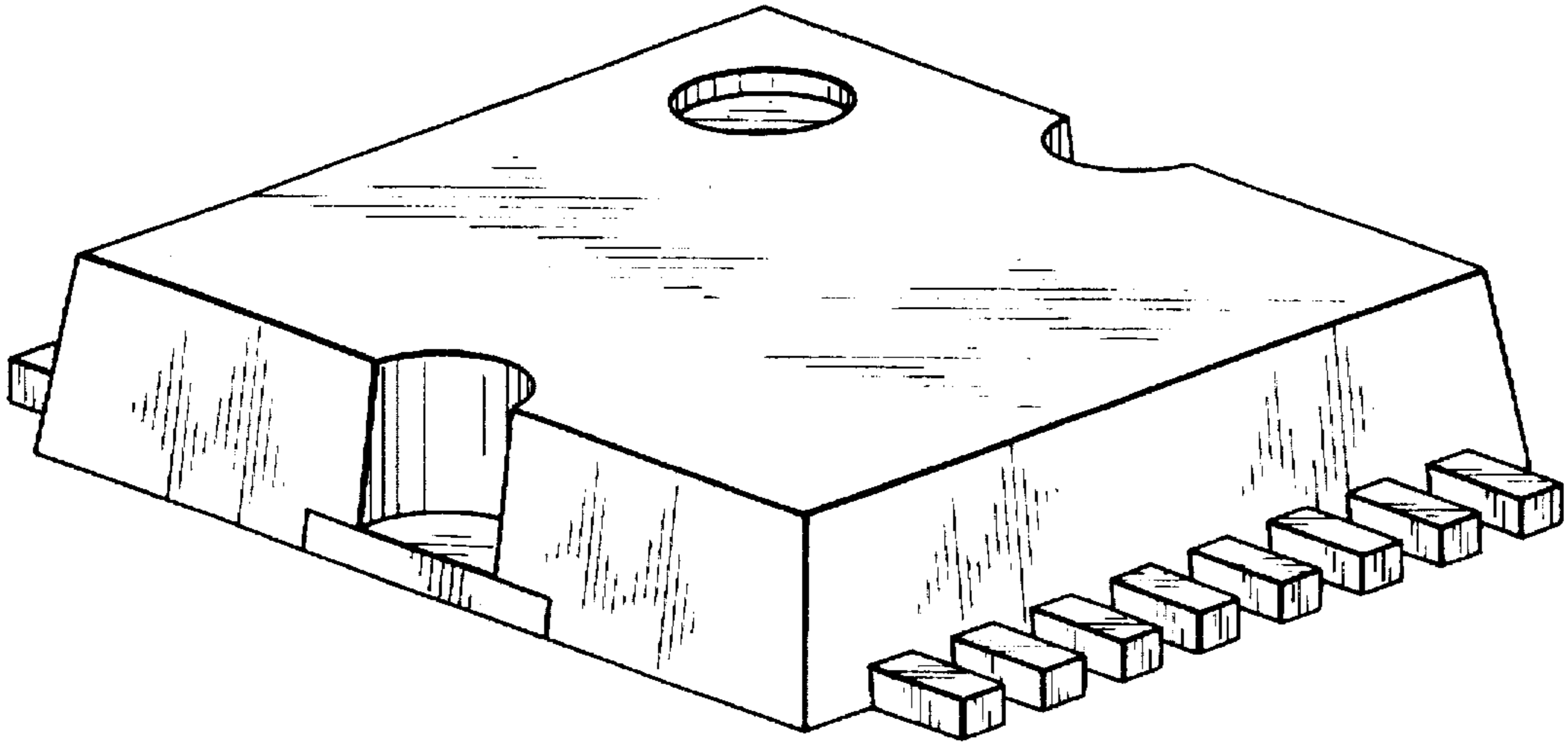


FIG. 2

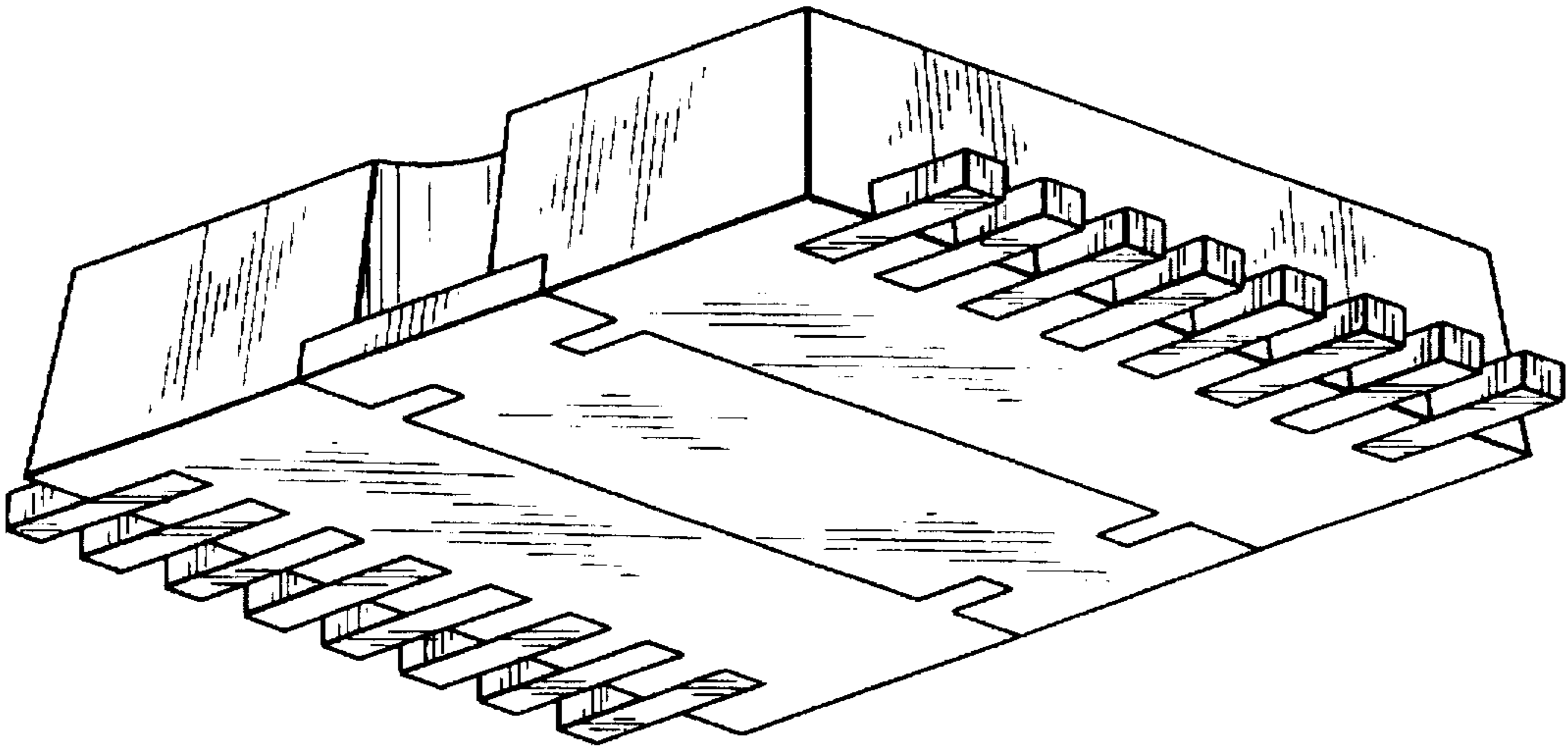


FIG. 3



FIG. 4

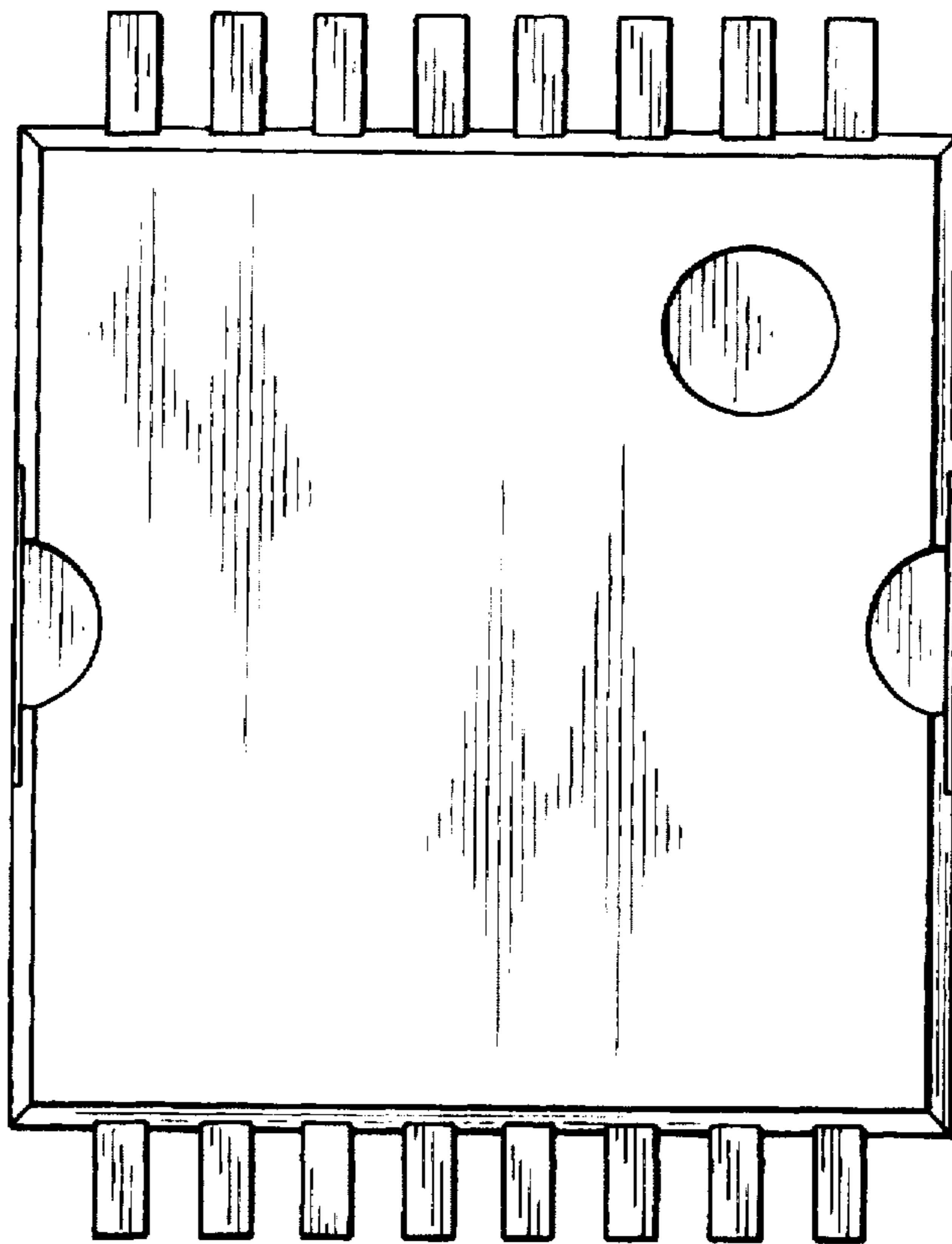


FIG. 5

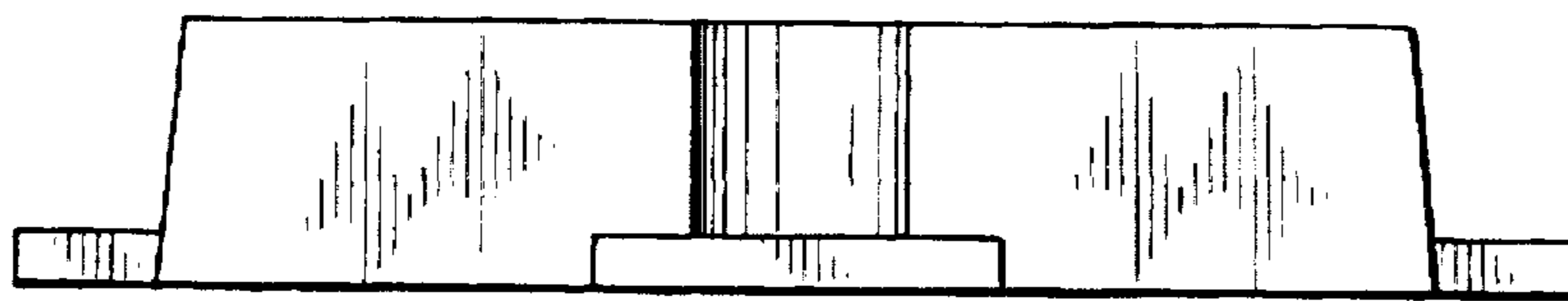


FIG. 6

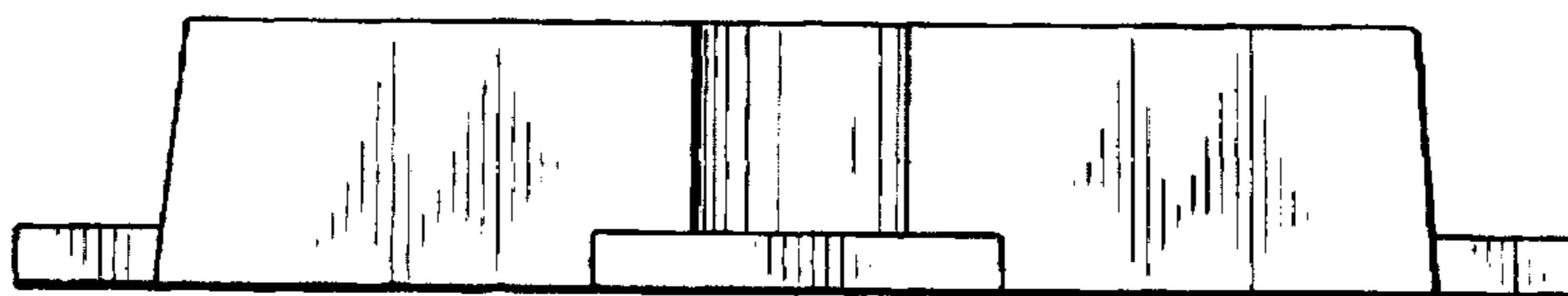


FIG. 7

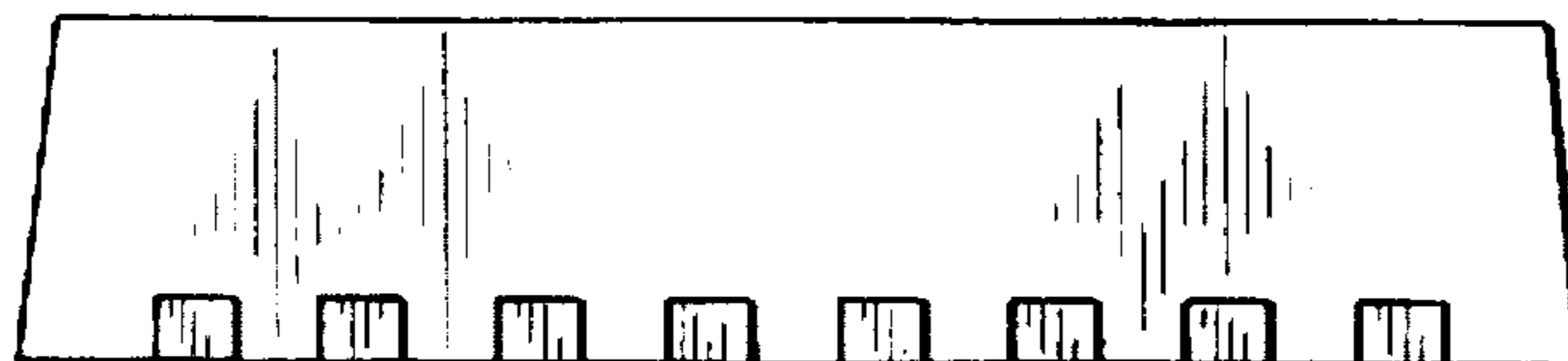


FIG. 8

